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Product Line:	Product Model: CLEAN TRACK™ LITHIUS Pro™ Z	Operation Type: Operator
Supplement for Theory of Operation Manual: Abbreviation List		

## › Supplement for Theory of Operation Manual: Abbreviation List

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When using the system or a manual, refer to the following table to check names and abbreviations.



### NOTE

Meanings of the alphabets in the classification column are as follows.

- B: Block name
- M: Module name

### ▼ Names and Abbreviations (in Alphabetical Order)

Abbre-viation	Complete Name	Classification
ABCT	Advanced Bottom Anti Reflection Coat Process Station	M
ACOT	Advanced Coat Process Station	M
ADEV	Advanced Develop Process Station	M
ADH	Adhesion Process Station	M
AITC	Advanced Immersion Top Coat Process Station	M
ANTD	Advanced Negatone Develop Process Station	M
BCT	Bottom Anti Reflection Coat Process Station	M
BST	Back Surface Treatment Process Station	M
BWEE	Wafer Edge Exposure Process Station + Bare-Si Thickness Monitor	M
CGCH	Chilling General-Purpose Hot Plate Process Station with Cover Heater	M
CGHP	Chilling General-Purpose Hot Plate Process Station	M
CGQH	Chilling General-Purpose Hot Plate Process Station with Cover Heater with Q series bowed wafer capability	M
CGQP	Chilling General-Purpose Hot Plate Process Station with Q series bowed wafer capability	M
CHBP	Chilling High temperature Hot Plate with VE Chamber Process Station For Bowed wafer	M
CHCH	Chilling High Temperature Hot Plate Process Station with Cover Heater	M
CHQP	Chilling High temperature Hot Plate with VE Chamber Process Station with Q series bowed wafer capability	M
CHVP	Chilling High temperature Hot Plate with VE Chamber Process Station	M
COT	Coat Process Station	M
CPHP	Chilling High Precision Hot Plate Process Station	M
CRA	Carrier station block robotic arm	M
CSB	Carrier Station Block	B
CSBP	Chilling Supreme Precision Hot Plate Process Station with Bowed Wafer Leveling	M
CSWP	Chilling Supreme Precision Hot Plate Process Station with Warpage Wafer Leveling	M
CVBP	Chilling Very High Temperature Hot Plate with VE Chamber Process Station For Bowed Wafer	M
CVCH	Chilling Very High Temperature Hot Plate Process Station with Cover Heater	M

<b>Abbre-viation</b>	<b>Complete Name</b>	<b>Classification</b>
CVQP	Chilling Very High Temperature Hot Plate with VE Chamber Process Station with Q series bowed wafer capability	M
CVVP	Chilling Very High temperature Hot Plate with VE Chamber Process Station	M
CWH	Cup Washer Holding Stage	M
CXHN	Chilling eXtreme High Temperature Hot Plate Process Station under Nitrogen Ambient	M
DEV	Develop Process Station	M
EIF	Exposure Interface	M
FOUP	Front opening unified pod	-
FPUP	FOUP Pick Up Stage	M
FRJC	FOUP Rejected Wafer Stage	M
FTRA	FOUP transfer robotic arm	M
FUST	FOUP Uni-Stage	M
ICPB	Interface Block Chill Plate Process Station with Bowed Wafer Leveling	M
ICPL	Interface Block Chill Plate Process Station	M
ICPQ	Interface Block Chill Plate Process Station with Q series bowed wafer capability	M
IFB	Interface Block	B
IRAI	Interface block robotic arm sub immersion	M
IRAM	Interface block robotic arm main	M
ITC	Immersion Top Coat Process Station	M
ITR	Immersion Top Remove Process Station	M
MMRA	Metrology integration block multi purpose robotic arm	M
MPB	Multi Purpose Block	B
MPRA	Multi purpose robotic arm	M
MRAS	Metrology integration block robotic arm sub	M
NTD	Negatone Develop Process Station	M
PIR	Post Immersion Rinse Process Station	M
PRA	Process block robotic arm	M
PRB	Process Block	B
RAQP	Chilling Advanced Precision Hot Plate Process Station with Q series bowed wafer capability Type-R	M
RPHP	Chilling High Precision Hot Plate Process Station Type-R	M
RPQP	Chilling High Precision Hot Plate Process Station with Q series bowed wafer capability Type-R	M
RSBC	Resuming Stage with Chilling with Bowed Wafer Leveling	M
RSBP	Chilling Supreme Precision Hot Plate Process Station with Bowed Wafer Leveling Type-R	M
RSM	Resuming Stage	M
RSMC	Resuming Chill Plate	M
RSQC	Resuming Stage with Chilling with Q series bowed wafer capability	M
RSQP	Chilling Supreme Precision Hot Plate Process Station with Q series bowed wafer capability Type-R	M
RSWP	Chilling Supreme Precision Hot Plate Process Station with Warpage Wafer Leveling Type-R	M
SBU	Stationary Buffering Stage	M
SCPB	Slim Chill Plate Process Station with Bowed Wafer Leveling	M
SCPL	Slim Chill Plate Process Station	M

<b>Abbre-viation</b>	<b>Complete Name</b>	<b>Classification</b>
SCPQ	Slim Chill Plate Process Station with Q series bowed wafer capability	M
SRS	Spin Rinse Process Station	M
TCT	Top Anti Reflection Coat Process Station	M
TRS	Transition Stage	M
WEE	Wafer Edge Exposure Process Station	M
WES	Wafer Edge Exposure Process Station Superior	M
WEX	Wafer Exchange Stage	M
WISC	Wafer Intelligent Scanner Inspection Module after Coating	M
WISD	Wafer Intelligent Scanner Inspection Module after Development	M
XLD	Exchanger FOUP Load Stage	M
XSTK	Exchanger FOUP Stocker	M
XULD	Exchanger FOUP Unload Stage	M

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